

SCOPE OF CLAIMS

1. A semiconductor device characterized in that:
a gate interconnection and a source interconnection are formed over a substrate
5 are disposed on the same plane; and
the gate interconnection and the source interconnection intersect through an insulating film in a region where the gate interconnection and the source interconnection intersect.
- 10 2. A semiconductor device characterized in that:
a gate interconnection and a source interconnection are formed over a substrate
are formed on the same plane; and
the gate interconnection and the source interconnection intersect through an island-like insulating film in a region where the gate interconnection and the source
15 interconnection intersect.
3. A semiconductor device comprising a source interconnection and a gate interconnection over a substrate, the semiconductor device characterized in that:
an island-like insulating film is formed between the gate interconnection and
20 the source interconnection in a region where the gate interconnection and the source interconnection intersect; and
the gate interconnection and the source interconnection are formed on a same insulating surface in a region where the gate interconnection and the source interconnection do not intersect.
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4. A semiconductor device according to claim 2 or 3 characterized in that:
the island-like insulating layer is formed so as to cover the gate interconnection
in a region where the gate interconnection and the source interconnection intersect; and

the source interconnection is formed over the island-like insulating layer.

5. A semiconductor device according to claim 2 or 3 characterized in that:

the island-like insulating layer is formed so as to cover the source
5 interconnection in a region where the gate interconnection and the source
interconnection intersect; and

the gate interconnection is formed over the island-like insulating layer.

6. A semiconductor device comprising a source region and a source
10 interconnection over a substrate, the semiconductor device characterized in that:

the source region and the source interconnection are connected on a same plane.

7. A semiconductor device according to claim 5 characterized in that:

the source region and the source interconnection are connected without through a
15 contact hole.

8. A semiconductor device according to any one of claims 1 to 3 characterized in
that:

at least one of the gate interconnection and the source interconnection is formed
20 by discharging a solution containing metal particles.

9. A semiconductor device according to any one of claims 1 to 3 characterized in
that:

at least one of the gate interconnection and the source interconnection is formed
25 by discharging a solution containing metal elements.

10. A semiconductor device according to claim 1 characterized in that:

the insulating film is formed by discharging a solution containing an insulating

material.

11. A semiconductor device according to any one of claims 2 and 3 characterized in that:

5 the island-like insulating layer is formed by discharging a solution containing an insulating material.

12. A semiconductor device according to any one of claims 1 to 3 and 5 characterized in that:

10 the semiconductor device includes a thin film transistor using a microcrystalline semiconductor.

13. A semiconductor device according to any one of claims 1 to 3 and 5 characterized in that:

15 the semiconductor device includes a thin film transistor using an organic semiconductor.

14. A method for manufacturing a semiconductor device characterized in that the semiconductor device is formed by the steps of:

20 forming a gate interconnection over a substrate;
forming an island-like insulating layer so as to selectively cover the gate interconnection; and
forming a source interconnection on a same plane of the gate interconnection,
wherein the gate interconnection and the source interconnection are formed so
25 as to intersect through the insulating layer in a region where the gate interconnection and the source interconnection intersect.

15. A method for manufacturing a semiconductor device characterized in that the

semiconductor device is formed by the steps of:

forming a source interconnection over a substrate;

forming an island-like insulating layer so as to selectively cover the source interconnection; and

- 5 forming a gate interconnection on a same plane of the source interconnection, wherein the source interconnection and the gate interconnection are formed so as to intersect through the insulating layer in a region where the source interconnection and the gate interconnection intersect.

- 10 16. A method for manufacturing a semiconductor device characterized in that the semiconductor device is formed by the steps of:

forming a gate interconnection over a substrate;

forming an island-like insulating layer so as to selectively cover the gate interconnection; and

- 15 forming a source interconnection on a same plane of the gate interconnection or the island-like insulating layer.

17. A method for manufacturing a semiconductor device according to any one of claims 14 to 16 characterized in that:

- 20 at least one of the gate interconnection or the source interconnection is formed by discharging a solution containing metal particles.

18. A method for manufacturing a semiconductor device according to any one of claims 14 to 16 characterized in that:

- 25 at least one of the gate interconnection or the source interconnection is formed by discharging a solution containing metal elements.

19. A method for manufacturing a semiconductor device according to any one of

claims 14 to 16 characterized in that:

the island-like insulating layer is formed by discharging a solution containing a insulating material.

5 20. A method for manufacturing a semiconductor device according to any one of claims 14 to 16 characterized in that:

the gate interconnection and the source interconnection are formed by using a laser drawing device.

10 21. A display device including the semiconductor device according to any one of claims 1 to 3 and 5.

22. A digital still camera including the semiconductor device according to any one of claims 1 to 3 and 5.

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23. A personal computer including the semiconductor device according to any one of claims 1 to 3 and 5.

24. A mobile computer including the semiconductor device according to any one
20 of claims 1 to 3 and 5.

25. An image reproducing system including the semiconductor device according to any one of claims 1 to 3 and 5.